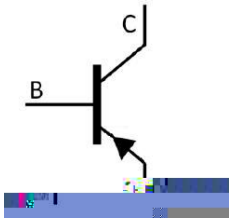
TO-126 PNP Silicon PNP transistor in a TO-126 Plastic Package.

V_{CEO}

High V_{CEO} Large DC current, high f_T, low $V_{CE(sat)}$.

Low power audio amplifier, high speed switching applications.



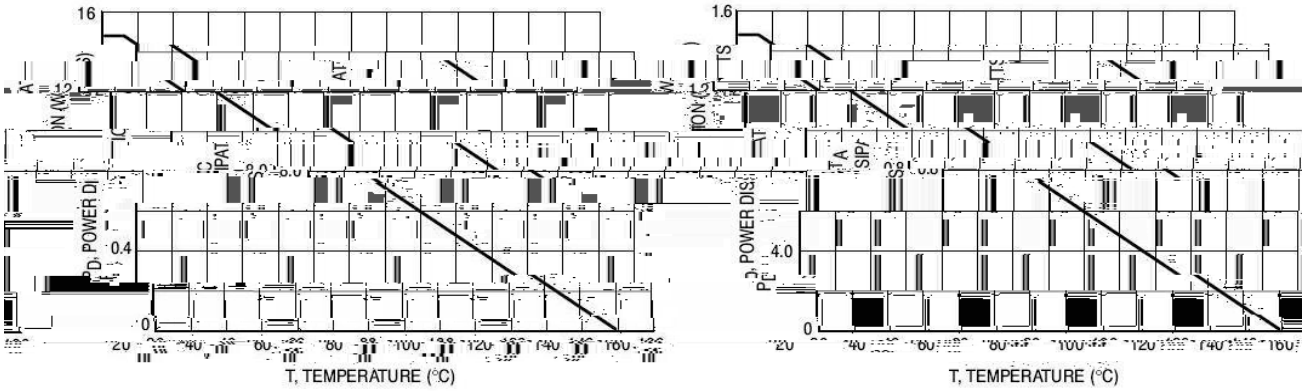


PIN1 Emitter PIN 2 Collector PIN 3 Base

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	$I_{C(1)}$	-4.0	A
	$I_{C(2)}$	-8.0	A
Peak Collector Current	I_B	-10	A
Collector Power Dissipation	P_D	1.5	W
Collector Power Dissipation	P_D(Tc=25)	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

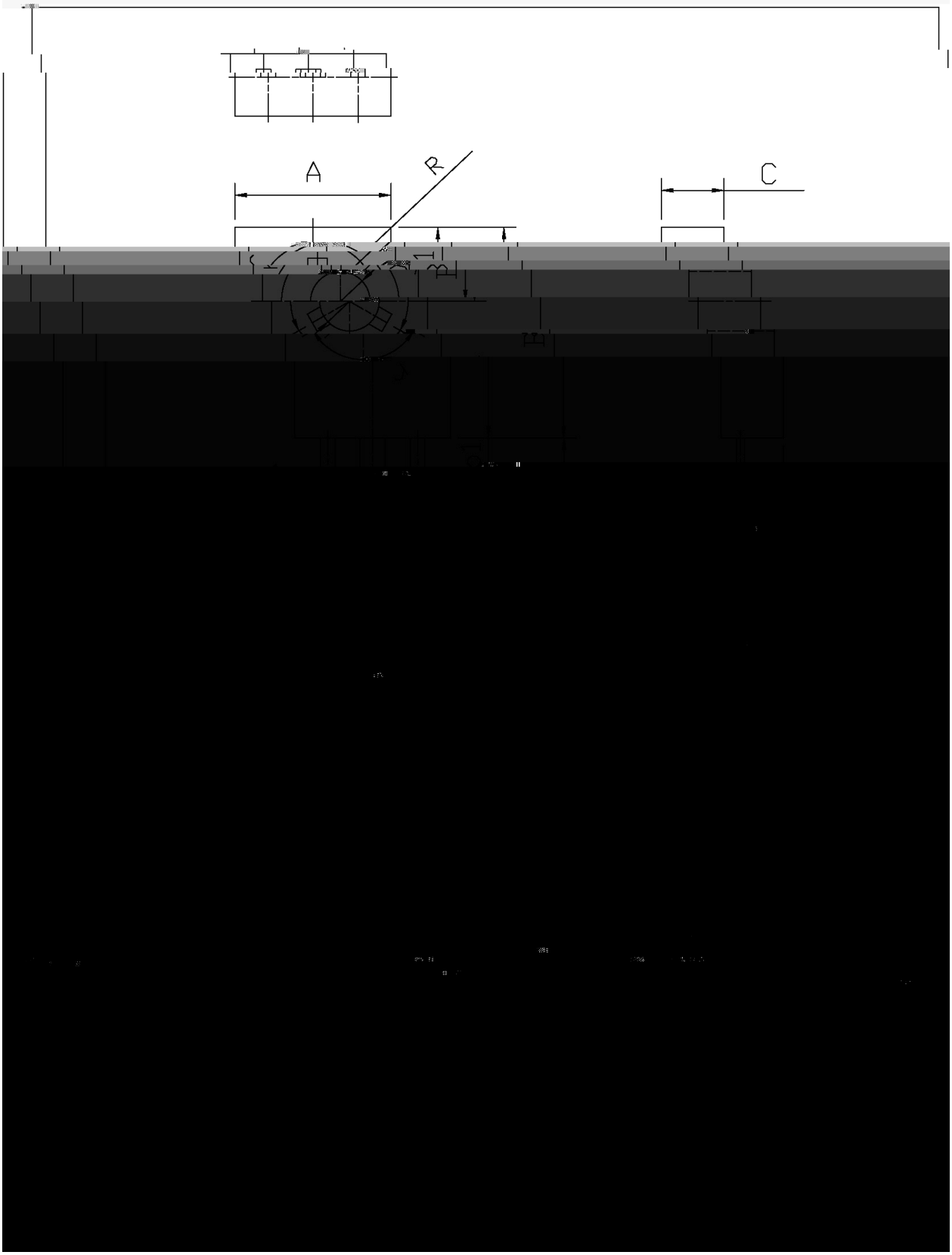
Parameter	Symbol	Test Conditions	Min

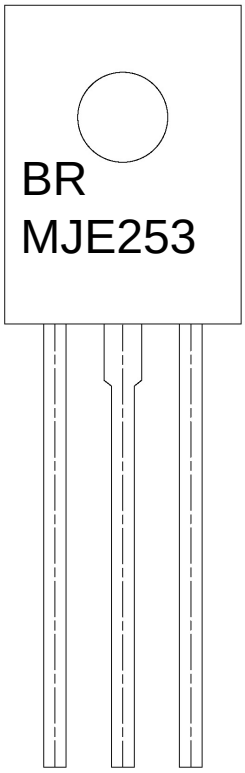

16
0.4
0
T, TEMPERATURE (°C)
1.6
4.0
0
T, TEMPERATURE (°C)


hFE – IC
200.
VCE = 1.0 V
IC – VCE
10
100 µs
500 µs
MJE253
hFE
10
7.0
5.0
0.05
0.02
IC
θV – IC
+2.5
V
TJ = 25°C

TO-126

单位：mm





BR

MJE253

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Note:

BR:	Company Code
MJE253:	Product Type.
****:	Lot No. Code, code change with Lot No.